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Agenda

- Effect of Oxygen on whisker surface
- Need for Compressive stress
- Inter-granular transport of Sn
- Inhibition mechanism of Pb
- Promotion mechanism by Zn, Cu and Mn
- Summary and conclusions

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Engineering use of models



Atomistic modeling provides inputs for FEA ad CFD



The (1 0 0) model



Surface oxygen puts whisker in tension



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I₁,The first invariant



(GPa)

$$\begin{bmatrix} -1.570 & 0 & 0 \\ 0 & -0.004 & 0 \\ 0 & 0 & -0.941 \end{bmatrix}$$

	К	E	G	
	Bulk	Young's	Shear	
	(GPa)	(GPa)	(GPa)	
MedeA	14	20	25	(1 0 0)
MedeA	50	55	21	β Sn
Literature	53	53	19	β Sn

$$I_1 = a_{11} + a_{22} + a_{33}$$
$$I_1 = -1.570 + -0.004 + -0.941 = -2.515$$

System I₁

		()
Sn ₁₂	(100)	-0.11
Sn ₁₂ C	04 (1 0 0)	-2.52

The first invariant, I₁,of the stress tensor describes expansion & contraction under hydrostatic loads

Whisker growth is marginal for stress relaxation compared to *plastic creep*



Pure tin strain rate vs Stress

Plastic creep often occurs faster than whisker growth

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The compressive stress paradox

- Local topographic features at whisker base generally do not change as the whisker grows
 - Suggests local compressive stress are not relieved by transferring local material into whisker.
- Hillocks form quickly, sufficient to reduce compressive stress
 - Boettinger, et al 2005
- Material in whiskers comes from the entire volume of tin
 - isotope studies by Woodrow 2006, 2009
- Creep rate of pure Tin is rapid with respect to whisker growth
 - Boettinger, et al 2005, Chalmers 1936, 1937
- Micro beam x-ray data showing compressive stress is relative to stress state of whisker.
 - Choi et al 2002
- Manganese alloys grow whiskers while in tension & continue to grow with out intergranular contact
 - Chen et al 2005



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Diffusion

- Woodrow showed us:
 - Tin transport between grains is fast
 - Whisker contains tin from a very large volume of basal tin
 - -2% (m/m) Pb does not seem to inhibit diffusion
- To get insight into Pb inhibition mechanism
 - Model diffusion of Sn on Sn and Pb surfaces
 - Model stability of Sn at & near Pb surface
 - Model stability of Pb at & near Sn surface
 - Model lone Sn atom at boundary between Pb & Sn surfaces
- These results lead to other models..... be patient....





Sn diffusion on Pb (111)





A really interesting result

Sn is more mobile along the whisker than across it



reported by J. Smetana, iNEMI Tin Whisker Workshop at

ECTC May 31 2005

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Sn diffusion on surfaces

•Sn on Sn (1 0 0) || to c-axis = 5

(kJmole<sup>-1</sup>)

•Sn on Sn (1 0 0) \perp to c-axis = 29

(kJmole<sup>-1</sup>)

•Sn on Pb (1 0 0) = 4.5 (kJmole<sup>-1</sup>)

•Pb on Pb (1 1 1) = 4.5 (kJmole<sup>-1</sup>)

•2 Sn on Sn (100) =141 (kJmole<sup>-1</sup>)

Concerted motion
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At 25 (°C): 159 Sn atoms out of every 160 Sn atoms move along the axis of the whisker.





Sn stability on Pb

Freeman, Materials Design



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Pb stability on Sn



Freeman, Materials Design



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Initial Grain Boundary Model Calculations

Freeman, Materials Design



Sn in Sn-Pb (1 0 0)

Pb in Sn-Sn (2 1 0)

Sn-Pb grain boundary collapses Glues surfaces & Traps Sn



Do we really know the driving force?

At 25 (°C):

 $E_{2} = 29 (kJ mol^{-1})$

- 13% of Sn atoms, have energy to move along Whisker length
- 0.0008% of Sn atoms have energy to move across whisker base
- Motion ∥ c-axis is 160 times more probable than motion ⊥ c-axis



- Most theories invoke compressive stress near base as driving force
 - Choi measured compressive stress
 - relative to whisker as neutral
 - Initial results showed no compressive stress at whisker base using published cell constants
 - Publishes stress map shows compressive stress > 400 (psi) at base of whisker
 - Chalmers reports compressive relaxation of single crystal tin (1935)
 - Yield limit near 100 to 200 (psi)
 - Creep is irreversible
 - Occurs in hours
 - Uses Hg diffusion along grain boundaries to separate crystals within minutes
- RMS work shows Oxygen on (100), (010) and (001) surfaces puts Sn in tension, with ~ 5% volume strain!

Anisotropic self diffusion promotes whiskers

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Ready? The next step is a BIG one!



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And now for something completely different....



– QUESTION: How much Pb is needed to 'stop' transport?



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Percolation

It's not just for coffee anymore!

- Percolation describes connectivity between adjacent sites
 - Describes:
 - Electrical conductivity of particles (e.g. filled polymers)
 - Modulus & strength of polymers
 - Diffusion & permeation
 - P_C : the critical point for properties
 - Electrical continuity
 - Gel point for polymers
 - Diffusion allowed / inhibited
 - **P**_c
 - ~ 0.5 for 2D square array
 - ~ 0.25 for 3D cubic array
 - But, Pb inhibits at 5% < Pb < 10% (m/m)...... Hmm....



Adjacent sites may, or may not be connected



A Sn Pb (dark) alloy

Sn diffuses between Sn grains... Does Pb create a percolation network?



An *infinite network* spans the sample at P = P_C

Why does 3% (m/m) Pb not inhibit whiskers?



3.5 %(v/v) Pb is about 6.5%(m/m) Pb, including solubility

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Percolation theory Scaling & experimental validation

- Scaling of percolation controlled observable
 - Electrical conductivity
 - Modulus
 - Isotope transport
 - Inverse Swiss cheese model
 - Electrical conductance scales as (P-P_c)^{1.3} and (P-P_c) ^{1.9} in 2D and 3D.
 - Modulus & mass transport scales as (P-P_c)^{1.3} and (P-P_c)^{1.4} in 2D and 3D.
- Experimental
 - Look for change in whisker induction stress
 - Isotope study of Sn transport using SIMS (Woodrow, Boeing)

Relationship between diffusion and percolation networks established.

TABLE I. Estimates of the differences between the transport percolation exponents in the continuum models $(\overline{t}, \overline{f}, \text{ and } \overline{e})$ and the corresponding exponents on a discrete lattice. Nonzero entries in the table correspond to the upper bounds in Eq. (5), and therefore are slight overestimates of the actual values. (a) The Swiss-cheese model; (b) the inverted Swiss-cheese or potential model.



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ASU: 5 wt% Pb Anode



Chawla & Williams, ASU

Exsolved Pb Volume Fraction Phase Diagram: 2.7% Image Analysis: 3.5%

Pb Cluster Sizes (μ m²) Mean: 2.5 Yellow: 20 - 30 (50 clusters) Blue: 30 - 40 (13 clusters) Green: 40 - 50 (5 clusters) Red: > 50 (2 clusters) Largest: 67



Inverse Swiss cheese Percolation network exists



ASU: 10 wt% Pb Anode

Chawla & Williams, ASU

00 um

Additional Pb improves percolation network

Exsolved Pb Volume Fraction Phase Diagram: 6.2% Image Analysis: 6.7%

Pb Cluster Sizes (μm^2) Mean: 2.9 Yellow: 20 – 30(101 clusters) Blue: 30 – 40 (33 clusters) Green: 40 – 50 (9 clusters) Red: > 50 (8 clusters) Largest: 81



Serial Sectioning Process Flow Chart (ASU)



Chawla & Williams, ASU





3D images of 10% (m/m0 Pb in Sn (ASU) Chawla & Williams, ASU



.... percolation network? You bet!



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Method

- Create a model grain boundary
 - Permit motion perpendicular to boundary
 - Pin all motion along boundary
 - Insert other metals, as a second phase, into boundary
 - Find the minimum energy configuration (relax)
 - Insert a lone tin atom into the second phase
 - Find the minimum energy configuration



The (1 0 0) model







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What does Zn do?



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Mn





Mn is known whisker Promoter Will grow whiskers after gaps develop between Sn grains



Why Mn alloys grow whiskers in tension



Mn is known whisker Promoter



Why Pb inhibits whiskers.....





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Summary

- Surface oxides put tin whisker in Tension
 - Whisker 'sucks' tin from base



- Pure tin relaxes by plastic creep within hours
- Diffusion of Tin along whisker is 160 times faster than diffusion across whisker base
- Inverse Swiss cheese model of percolation explains
 - > 3.5% (v/v) of second phase is needed to establish infinite network
 - This is 6.5% (m/m) Pb, including RT solubility
- Pb appears to 'trap' Sn
- Mn, & Zn appear to open channels
- Atomistic modeling is a useful tool for persistent problems



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